Toyohiro Chikyow

List of Publications by Citations

282 papers	6,425 citations	33 h-index	74 g-index
306 ext. papers	6,864 ext. citations	3.3 avg, IF	5.5 L-index

#	Paper	IF	Citations
282	Room-temperature ferromagnetism in transparent transition metal-doped titanium dioxide. *Science*, **2001**, 291, 854-6	33.3	2208
281	New MBE growth method for InSb quantum well boxes. *Journal of Crystal Growth*, **1991**, 111, 688-692	1.6	293
280	Anomalous Hall effect governed by electron doping in a room-temperature transparent ferromagnetic semiconductor. *Nature Materials*, **2004**, 3, 221-4	27	214
279	Recent advances in Prussian blue and Prussian blue analogues: synthesis and thermal treatments. *Coordination Chemistry Reviews*, **2017**, 352, 328-345	23.2	152
278	Evolution of standing mesochannels on porous anodic alumina substrates with designed conical holes. *Journal of the American Chemical Society*, **2008**, 130, 10165-70	16.4	127
277	First-principles studies of the intrinsic effect of nitrogen atoms on reduction in gate leakage current through Hf-based high-k dielectrics. *Applied Physics Letters*, **2005**, 86, 143507	3.4	127
276	Oxygen Vacancy Induced Substantial Threshold Voltage Shifts in the Hf-based High-KMISFET with p+poly-Si Gates -A Theoretical Approach. *Japanese Journal of Applied Physics*, **2004**, 43, L1413-L1415	1.4	117
275	Impact of Cu Electrode on Switching Behavior in a Cu/HfO2/Pt Structure and Resultant Cu Ion Diffusion. *Applied Physics Express*, **2009**, 2, 061401	2.4	95
274	Modified Oxygen Vacancy Induced Fermi Level Pinning Model Extendable to P-Metal Pinning. *Japanese Journal of Applied Physics*, **2006**, 45, L1289-L1292	1.4	92
273	Optically and electrically driven organic thin film transistors with diarylethene photochromic channel layers. *ACS Applied Materials & Interfaces*, **2013**, 5, 3625-30	9.5	71
272	Formation of a K-In-Se Surface Species by NaF/KF Postdeposition Treatment of Cu(In,Ga)Se Thin-Film Solar Cell Absorbers. *ACS Applied Materials & Interfaces*, **2017**, 9, 3581-3589	9.5	70
271	Cobalt valence states and origins of ferromagnetism in Co doped TiO2 rutile thin films. *Journal of Applied Physics*, **2004**, 95, 5330-5333	2.5	67
270	Effect of UV□ozone treatment on electrical properties of PEDOT:PSS film. *Organic Electronics*, **2011**, 12, 279-284	3.5	66
269	MBE Growth Method for Pyramid-Shaped GaAs Micro Crystals on ZnSe(001) Surface Using Ga Droplets. *Japanese Journal of Applied Physics*, **1990**, 29, L2093-L2095	1.4	65
268	Depletion of the In2O3(001) and (111) surface electron accumulation by an oxygen plasma surface treatment. *Applied Physics Letters*, **2011**, 98, 172101	3.4	62
267	Magneto-Optical Spectroscopy of Anatase TiO2Doped with Co. *Japanese Journal of Applied Physics*, **2003**, 42, L105-L107	1.4	60
266	Multi-Valued Logic Circuits Based on Organic Anti-ambipolar Transistors. *Nano Letters*, **2018**, 18, 4355-4359	11.5	58

265	Suppression of oxygen vacancy formation in Hf-based high-k dielectrics by lanthanum incorporation. *Applied Physics Letters*, **2007**, 91, 132904	3.4	57
264	Oxygen migration at Pt/HfO2/Pt interface under bias operation. *Applied Physics Letters*, **2010**, 97, 082903	3.4	55
263	Optical switching of carrier transport in polymeric transistors with photochromic spiropyran molecules. *Journal of Materials Chemistry C*, **2013**, 1, 3012	7.1	53
262	Bias application hard x-ray photoelectron spectroscopy study of forming process of Cu/HfO2/Pt resistive random access memory structure. *Applied Physics Letters*, **2011**, 99, 223517	3.4	53
261	Amorphous stability of HfO2 based ternary and binary composition spread oxide films as alternative gate dielectrics. *Applied Surface Science*, **2004**, 223, 229-232	6.7	49
260	Highly Uniform Epitaxial ZnO Nanorod Arrays for Nanopiezotronics. *Nanoscale Research Letters*, **2009**, 4, 699-704	5	47
259	Continuous synthesis of organic-inorganic hybridized cubic nanoassemblies of octahedral cerium oxide nanocrystals and hexanedioic acid. *Dalton Transactions*, **2008**, 5442-6	4.3	47
258	Generalized mechanism of the resistance switching in binary-oxide-based resistive random-access memories. *Physical Review B*, **2013**, 87,	3.3	45
257	Negative Differential Resistance Transistor with Organic p-n Heterojunction. *Advanced Electronic Materials*, **2017**, 3, 1700106	6.4	44
256	Improvement in ferroelectricity of HfxZr1−xO2thin films using ZrO2seed layer. *Applied Physics Express*, **2017**, 10, 081501	2.4	43
255	Oxygen-vacancy-induced threshold voltage shifts in Hf-related high-k gate stacks. *Thin Solid Films*, **2006**, 508, 305-310	2.2	39
254	XPS study of Sb-/In-doping and surface pinning effects on the Fermi level in SnO2 (101) thin films. *Applied Physics Letters*, **2011**, 98, 232107	3.4	37
253	Continuous hydrothermal synthesis of nickel oxide nanoplates and their use as nanoinks for p-type channel material in a bottom-gate field-effect transistor. *Nanotechnology*, **2010**, 21, 134009	3.4	35
252	Unique device operations by combining optical-memory effect and electrical-gate modulation in a photochromism-based dual-gate transistor. *ACS Applied Materials & Interfaces*, **2013**, 5, 9726-31	9.5	34
251	Perfect Bi4Ti3O12 Single-Crystal Films via Flux-Mediated Epitaxy. *Advanced Functional Materials*, **2006**, 16, 485-491	15.6	34
250	Field-effect modulation of the transport properties of nondoped SrTiO3. *Applied Physics Letters*, **2006**, 88, 212116	3.4	33
249	Self-assembled molecular nanowires of 6,13-Bis(methylthio)pentacene: growth, electrical properties, and applications. *Nano Letters*, **2008**, 8, 3273-7	11.5	31
248	Interface engineering for the passivation of c-Si with O3-based atomic layer deposited AlOx for solar cell application. *Applied Physics Letters*, **2012**, 100, 143901	3.4	28

247	High-Quality p-Type ZnO Films Grown by Co-Doping of N and Te on Zn-Face ZnO Substrates. *Applied Physics Express*, **2010**, 3, 031103	2.4	28
246	A combinatorial approach in oxide/semiconductor interface research for future electronic devices. *Applied Surface Science*, **2002**, 189, 284-291	6.7	27
245	Early Stage of Growth of a Perylene Diimide Derivative Thin Film Growth on Various Si(001) Substrates. *Journal of Physical Chemistry C*, **2007**, 111, 12747-12751	3.8	26
244	Perspective: Highly ordered MoS2 thin films grown by multi-step chemical vapor deposition process. *APL Materials*, **2016**, 4, 030901	5.7	25
243	Device Geometry Engineering for Controlling Organic Antiambipolar Transistor Properties. *Journal of Physical Chemistry C*, **2018**, 122, 6943-6946	3.8	24
242	Photoelectron spectroscopic study of band alignment of polymer/ZnO photovoltaic device structure. *Applied Physics Letters*, **2013**, 102, 043302	3.4	24
241	Energy-level alignments and photo-induced carrier processes at the heteromolecular interface of quaterrylene and N,N'-dioctyl-3,4,9,10-perylenedicarboximide. *Physical Chemistry Chemical Physics*, **2011**, 13, 6280-5	3.6	24
240	Fabrication of three-component composition spread thin film with controlled composition and thickness. *Applied Physics A: Materials Science and Processing*, **2004**, 79, 837-839	2.6	24
239	Mathematical design of linear action masks for binary and ternary composition spread film library. *Applied Surface Science*, **2004**, 223, 9-13	6.7	24
238	Effects of nitrogen atom doping on dielectric constants of Hf-based gate oxides. *Applied Physics Letters*, **2006**, 88, 112903	3.4	23
237	Development of scanning microwave microscope with a lumped-constant resonator probe for high-throughput characterization of combinatorial dielectric materials. *Applied Surface Science*, **2002**, 189, 222-226	6.7	23
236	Improvement in carrier mobility of poly(3,4-ethylenedioxythiophene) nanowires synthesized in porous alumina templates. *Journal of Polymer Science, Part B: Polymer Physics*, **2011**, 49, 1762-1768	2.6	22
235	Growth of anthracene derivative thin films with a □stacking structure. *Applied Physics Letters*, **2006**, 88, 081907	3.4	22
234	Optically controllable dual-gate organic transistor produced via phase separation between polymer semiconductor and photochromic spiropyran molecules. *ACS Applied Materials & Interfaces*, **2014**, 6, 10415-20	9.5	21
233	Combinatorial study of Ni□Ti□Pt ternary metal gate electrodes on HfO2 for the advanced gate stack. *Applied Physics Letters*, **2006**, 89, 142108	3.4	21
232	A practical treatment for the three-body interactions in the transcorrelated variational Monte Carlo method: application to atoms from lithium to neon. *Journal of Chemical Physics*, **2005**, 122, 224101	3.9	21
231	Interface engineering for improving optical switching in a diarylethene-channel transistor. *Organic Electronics*, **2015**, 21, 149-154	3.5	20
230	Interface Engineering for Controlling Device Properties of Organic Antiambipolar Transistors. *ACS Applied Materials & Interfaces*, **2018**, 10, 2762-2767	9.5	20

229	Hard x-ray photoelectron spectroscopy study on band alignment at poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate)/ZnO interface. *Applied Physics Letters*, **2012**, 101, 173303	3.4	20
228	XPS study on band alignment at Pt?O-terminated ZnO(0001) interface. *Surface and Interface Analysis*, **2010**, 42, 1528-1531	1.5	20
227	Optimizing optical absorption of TiO2 by alloying with TiS2. *Applied Physics Letters*, **2008**, 92, 041104	3.4	20
226	Microcrystal growth of GaAs on a Se-terminated GaAlAs surface for the quantum-well box structure by sequential supplies of Ga and As molecular beams. *Applied Physics Letters*, **1992**, 61, 2431-2433	3.4	20
225	Crystal structures and band offsets of ultrathin HfO2Y2O3 composite films studied by photoemission and x-ray absorption spectroscopies. *Applied Physics Letters*, **2006**, 89, 172107	3.4	19
224	Single-Electron Tunneling through Molecular Quantum Dots in a Metal-Insulator-Semiconductor Structure. *Advanced Functional Materials*, **2011**, 21, 2933-2937	15.6	18
223	Characterization of HfSiON gate dielectrics using monoenergetic positron beams. *Journal of Applied Physics*, **2006**, 99, 054507	2.5	18
222	Heteroepitaxial Growth of Rutile TiO2on GaN(0001) by Pulsed Laser Deposition. *Japanese Journal of Applied Physics*, **2005**, 44, L1503-L1505	1.4	18
221	Resistive switching characteristics in memristors with Al2O3/TiO2and TiO2/Al2O3bilayers. *Japanese Journal of Applied Physics*, **2016**, 55, 08PB02	1.4	17
220	Interface structure and the chemical states of Pt film on polar-ZnO single crystal. *Applied Physics Letters*, **2009**, 94, 221904	3.4	17
219	Influences of annealing in reducing and oxidizing ambients on flatband voltage properties of HfO2 gate stack structures. *Journal of Applied Physics*, **2007**, 101, 084118	2.5	17
218	Bias-voltage application in a hard x-ray photoelectron spectroscopic study of the interface states at oxide/Si(100) interfaces. *Journal of Applied Physics*, **2013**, 113, 163707	2.5	16
217	Growth of quaterrylene thin films on a silicon dioxide surface using vacuum deposition. *Organic Electronics*, **2007**, 8, 631-634	3.5	16
216	Annealing properties of open volumes in HfSiOx and HfAlOx gate dielectrics studied using monoenergetic positron beams. *Journal of Applied Physics*, **2005**, 98, 023506	2.5	16
215	Possible Ferroelectricity in SnTiO3 by First-Principles Calculations. *Materials Research Society Symposia Proceedings*, **2002**, 748, 1		16
214	Rapid Synthesis and Scanning Probe Analysis of BaxSr1-xTiO3 Composition Spread Films on a Temperature Gradient Si(100) Substrate. *Japanese Journal of Applied Physics*, **2002**, 41, L149-L151	1.4	16
213	Synthesis of Hollow Co-Fe Prussian Blue Analogue Cubes by using Silica Spheres as a Sacrificial Template. *ChemistryOpen*, **2018**, 7, 599-603	2.3	15
212	Through silicon via filling methods with metal/polymer composite for three-dimensional LSI. *Japanese Journal of Applied Physics*, **2014**, 53, 06JH01	1.4	15

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209	Interface engineering for molecular alignment and device performance of quaterrylene thin films. *Applied Physics Letters*, **2008**, 93, 153301	3.4	15
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207	Role of Nitrogen Incorporation into Hf-Based High-kGate Dielectrics for Termination of Local Current Leakage Paths. *Japanese Journal of Applied Physics*, **2005**, 44, L1333-L1336	1.4	15
206	Cyanide bridged coordination polymer nanoflakes thermally derived Ni3C and fcc-Ni nanoparticles for electrocatalysts. *New Journal of Chemistry*, **2017**, 41, 14890-14897	3.6	14
205	Cross-sectional TEM study and film thickness dependence of Tc in heavily boron-doped superconducting diamond. *Physica C: Superconductivity and Its Applications*, **2010**, 470, S610-S612	1.3	14
204	Isotopic labeling study of the oxygen diffusion in HfO2SiO2Si. *Applied Physics Letters*, **2007**, 90, 133510	3.4	14
203	Strain-effect for controlled growth mode and well-ordered structure of quaterrylene thin films. *Journal of Chemical Physics*, **2010**, 133, 034706	3.9	13
202	Chemical controllability of charge states of nitrogen-related defects in HfOxNy: First-principles calculations. *Physical Review B*, **2008**, 77,	3.3	13
201	Hafnium 4f Core-level Shifts Caused by Nitrogen Incorporation in Hf-based High-kGate Dielectrics. *Japanese Journal of Applied Physics*, **2007**, 46, 3507-3509	1.4	13
200	High-throughput screening of combinatorial materials libraries by high-energy x-ray diffraction. *Applied Physics Letters*, **2007**, 91, 071916	3.4	13
199	Adhesion of silver/polypyrrole nanocomposite coating to a fluoropolymer substrate. *Applied Surface Science*, **2016**, 384, 492-496	6.7	13
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197	Mn Self-Doping of Orthorhombic RMnO Perovskites: (RMn)MnO with R = Er-Lu. *Inorganic Chemistry*, **2018**, 57, 2773-2781	5.1	12
196	Photoisomerization-induced manipulation of single-electron tunneling for novel Si-based optical memory. *ACS Applied Materials & Interfaces*, **2013**, 5, 11371-6	9.5	12
195	Epitaxial growth of nonpolar ZnO and n-ZnO/i-ZnO/p-GaN heterostructure on Si(001) for ultraviolet light emitting diodes. *Applied Physics Express*, **2014**, 7, 062102	2.4	12
194	Influence of the substrate choice on the L10 phase formation of post-annealed Pt/Fe and Pt/Ag/Fe thin films. *Journal of Applied Physics*, **2014**, 116, 044310	2.5	12

193	Composition-spread thin films of pentacene and 6,13-pentacenequinone fabricated by using continuous-wave laser molecular beam epitaxy. *Applied Surface Science*, **2008**, 254, 2336-2341	6.7	12
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191	Combinatorial screening of ternary NiO□Mn2O3□CuO composition spreads. *Journal of Applied Physics*, **2005**, 98, 043710	2.5	12
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186	Stress Release Drives Growth Transition of Quaterrylene Thin Films on SiO2 Surfaces. *Journal of Physical Chemistry C*, **2009**, 113, 2197-2199	3.8	10
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184	Microstructure and interface control of GaN/MgAl2O4 grown by metalorganic chemical vapor deposition: Substrate-orientation dependence. *Journal of Applied Physics*, **2011**, 110, 023504	2.5	10
183	Effect of Annealing on Implanted Ga of Diamond-Like Carbon Thin Films Fabricated by Focused-Ion-Beam Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2008**, 47, 9010-9012	1.4	10
182	Analysis of carrier transport in quaterrylene thin film transistors formed by ultraslow vacuum deposition. *Journal of Applied Physics*, **2008**, 104, 024506	2.5	10
181	Evolution of Quaterrylene Thin Films on a Silicon Dioxide Surface Using an Ultraslow Deposition Technique. *Journal of Physical Chemistry C*, **2007**, 111, 18703-18707	3.8	10
180	Thermal stability of Ni silicide films on heavily doped n+ and p+ Si substrates. *Microelectronic Engineering*, **2008**, 85, 1642-1646	2.5	10
179	GaAs microcrystal growth on semiconductor surfaces by low energy focused ion beam. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **1998**, 16, 2538		10
178	BaTiO3 based relaxor ferroelectric epitaxial thin-films for high-temperature operational capacitors. *Japanese Journal of Applied Physics*, **2015**, 54, 04DH02	1.4	9
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176	Chemical Synthesis of Multilayered Nanostructured Perovskite Thin Films with Dielectric Features for Electric Capacitors. *ACS Applied Nano Materials*, **2018**, 1, 915-921	5.6	9

175	Graphene-Wrapped Nanoporous Nickel-Cobalt Oxide Flakes for Electrochemical Supercapacitors. *ChemistrySelect*, **2018**, 3, 8505-8510	1.8	9
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173	Adsorption structure of phenylphosphonic acid on an alumina surface. *Applied Surface Science*, **2009** , 256, 1140-1143	6.7	9
172	Fully engineered homoepitaxial zinc oxide nanopillar array for near-surface light wave manipulation. *Applied Physics Letters*, **2008**, 92, 183114	3.4	9
171	Impact of nitridation on open volumes in HfSiOx studied using monoenergetic positron beams. *Applied Physics Letters*, **2006**, 88, 171912	3.4	9
170	Epitaxial Growth of the Wurtzite $(11bar{2}0)$ AlN Thin Films on Si(100) with MnS Buffer Layer. *Japanese Journal of Applied Physics*, **2002**, 41, L1291-L1293	1.4	9
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168	Conductive polymer/metal composites for interconnect of flexible devices. *Japanese Journal of Applied Physics*, **2015**, 54, 06FJ12	1.4	8
167	Nanochannel effect in polymer nanowire transistor with highly aligned polymer chains. *Applied Physics Letters*, **2015**, 106, 243301	3.4	8
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165	Structural analysis and transistor properties of hetero-molecular bilayers. *Thin Solid Films*, **2009**, 518, 441-443	2.2	8
164	Diffusion induced amorphization in the crystalline SrTiO3 thin films grown on Si (1 0 0) investigated by combinatorial method. *Applied Surface Science*, **2002**, 189, 307-312	6.7	8
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162	Diffusion barrier and adhesion properties of SiO(x)N(y) and SiO(x) layers between Ag/polypyrrole composites and Si substrates. *ACS Applied Materials & Interfaces*, **2014**, 6, 9201-6	9.5	7
161	Influence of oxygen transfer in Hf-based high-k dielectrics on flatband voltage shift. *Thin Solid Films* , **2012**, 520, 3387-3391	2.2	7
160	Epitaxial CeO2 thin films for a mechanism study of resistive random access memory (ReRAM). *Journal of Solid State Electrochemistry*, **2013**, 17, 3137-3144	2.6	7
159	Prediction of optically-active transitions in type-VIII guest-free silicon clathrate Si46: A comparative study of its physical properties with type-I counterpart through first-principles. *Journal of Applied Physics*, **2017**, 122, 205103	2.5	7
158	Interface chemistry and electronic structure of GaN/MgAl2O4 revealed by angle-resolved photoemission spectroscopy. *Applied Physics Letters*, **2010**, 97, 161907	3.4	7

157	Fast Formation of Conductive Material by Simultaneous Chemical Process for Infilling Through-Silicon Via. *Japanese Journal of Applied Physics*, **2012**, 51, 06FG11	1.4	7
156	Characterization of Metal/High-kStructures Using Monoenergetic Positron Beams. *Japanese Journal of Applied Physics*, **2007**, 46, 3214-3218	1.4	7
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153	Epitaxial growth of high dielectric constant lead-free relaxor ferroelectric for high-temperature operational film capacitor. *Thin Solid Films*, **2015**, 592, 29-33	2.2	6
152	Multilevel Operation of Resonant Tunneling with Binary Molecules in a MetalInsulatorSemiconductor Configuration. *Journal of Physical Chemistry C*, **2014**, 118, 6467-6472	3.8	6
151	Influence of Al2O3 layer insertion on the electrical properties of Ga-In-Zn-O thin-film transistors. *Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films*, **2015**, 33, 061506	2.9	6
150	A Numerical Formula for General Prediction of Interface Bonding between Alumina and Aluminum-Containing Alloys. *International Journal of Metals*, **2014**, 2014, 1-11		6
149	Schottky barrier height behavior of PtRu alloy contacts on single-crystal n-ZnO. *Journal of Applied Physics*, **2010**, 107, 103714	2.5	6
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144	Surface structure dependence of GaAs microcrystals size grown by As-incorporation into Ga droplets. *Surface Science*, **1992**, 267, 241-244	1.8	6
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141	Mesostructured HfO/AlO Composite Thin Films with Reduced Leakage Current for Ion-Conducting Devices. *ACS Omega*, **2019**, 4, 14680-14687	3.9	5
140	Molecular magnetic thin films made from Ni-Co Prussian blue analogue anchored on silicon wafers. *Journal of Magnetism and Magnetic Materials*, **2019**, 486, 165276	2.8	5

139	Photoelectron spectroscopic study of electronic states and surface structure of an in situ cleaved In2O3 (111) single crystal. *Japanese Journal of Applied Physics*, **2019**, 58, SDDG06	1.4	5
138	Photoelectron spectroscopic study on electronic state and electrical properties of SnO2 single crystals. *Japanese Journal of Applied Physics*, **2019**, 58, 080903	1.4	5
137	Cathodoluminescence and field emission from GaN/MgAl2O4 grown by metalorganic chemical vapor deposition: substrate-orientation dependence. *Journal of Materials Chemistry C*, **2013**, 1, 238-245	7.1	5
136	P-type polymer-based Ag2S atomic switch for Ëug of warÐperation. *Japanese Journal of Applied Physics*, **2017**, 56, 06GF03	1.4	5
135	Relationship between passivation properties and band alignment in O3-based atomic-layer-deposited AlOxon crystalline Si for photovoltaic applications. *Japanese Journal of Applied Physics*, **2015**, 54, 08KD19	1.4	5
134	Effect of niobium doping on the optical and electrical properties in titanium dioxide grown by pulsed laser deposition. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2012**, 30, 050603	1.3	5
133	Observation of filament formation process of Cu/HfO2/Pt ReRAM structure by hard x-ray photoelectron spectroscopy under bias operation. *Journal of Materials Research*, **2012**, 27, 869-878	2.5	5
132	Combinatorial synthesis of Cu/(Ta(x)Nb(1-x))2O5 stack structure for nanoionics-type ReRAM device. *ACS Combinatorial Science*, **2013**, 15, 435-8	3.9	5
131	Variable temperature characterization of N,N?-Bis(n-pentyl)terrylene-3,4:11,12-tetracarboxylic diimide thin film transistor. *Organic Electronics*, **2009**, 10, 1187-1190	3.5	5
130	Synthesis of octabutoxyphthalocyanine nanorods using porous alumina as a template and magnetic-field-directed control of the molecular orientation in the nanorods. *Journal of Materials Chemistry*, **2008**, 18, 4347		5
129	Pliant Epitaxial Ionic Oxides on Silicon. *Advanced Materials*, **2008**, 20, 3827-3831	24	5
128	Role of the one-body Jastrow factor in the transcorrelated self-consistent field equation. *International Journal of Quantum Chemistry*, **2006**, 106, 1477-1486	2.1	5
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